

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2SA1201

POWER AMPLIFIER APPLICATIONS

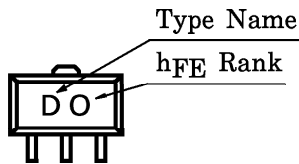
- High Voltage : $V_{CEO} = -120V$
- High Transition Frequency : $f_T = 120MHz$ (Typ.)
- $P_C = 1\sim 2W$ (Mounted on Ceramic Substrate)
- Small Flat Package
- Complementary to 2SC2881

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-120	V
Collector-Emitter Voltage	V_{CEO}	-120	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-800	mA
Base Current	I_B	-160	mA
Collector Power Dissipation	P_C	500	mW
Collector Power Dissipation	P_C^*	1000	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$

 P_C^* : Mounted on ceramic substrate ($250mm^2 \times 0.8t$)

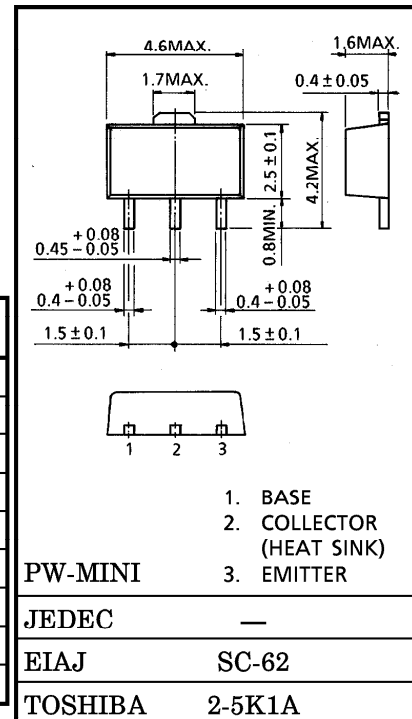
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ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -120V, I_E = 0$	—	—	-0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$	—	—	-0.1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR) CEO}$	$I_C = -10mA, I_B = 0$	-120	—	—	V
Emitter-Base Breakdown Voltage	$V_{(BR) EBO}$	$I_E = -1mA, I_C = 0$	-5	—	—	V
DC Current Gain	h_{FE} (Note)	$V_{CE} = -5V, I_C = -100mA$	80	—	240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$	—	—	-1.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -5V, I_C = -500mA$	—	—	-1.0	V
Transition Frequency	f_T	$V_{CE} = -5V, I_C = -100mA$	—	120	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	—	—	30	pF

Note : h_{FE} Classification O : 80~160, Y : 120~240

Unit in mm



PW-MINI

JEDEC

EIAJ

TOSHIBA

1. BASE
2. COLLECTOR (HEAT SINK)
3. EMITTER

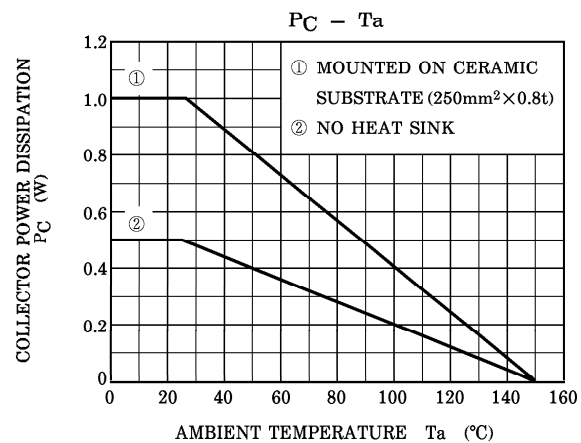
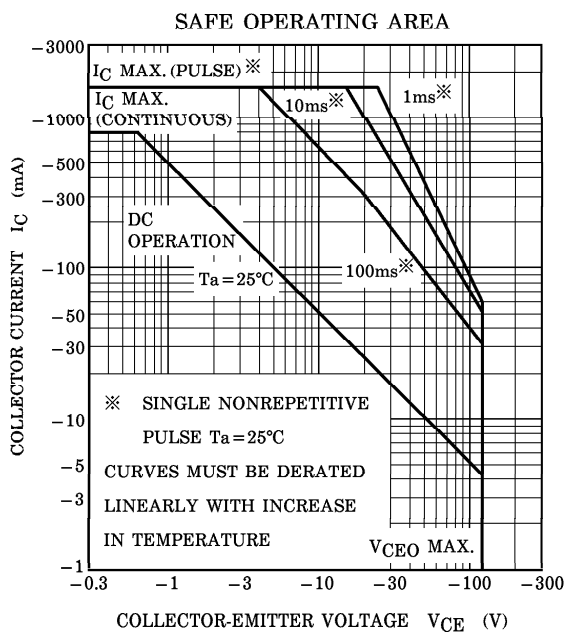
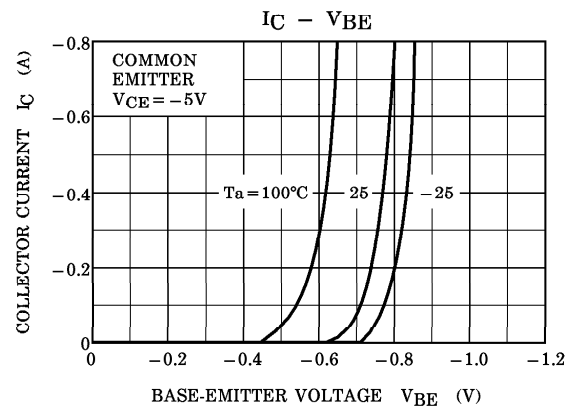
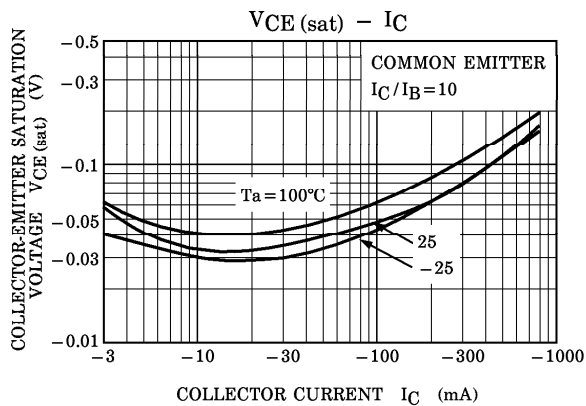
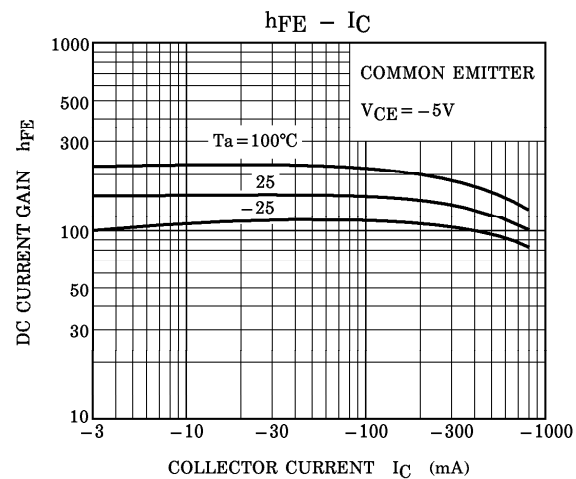
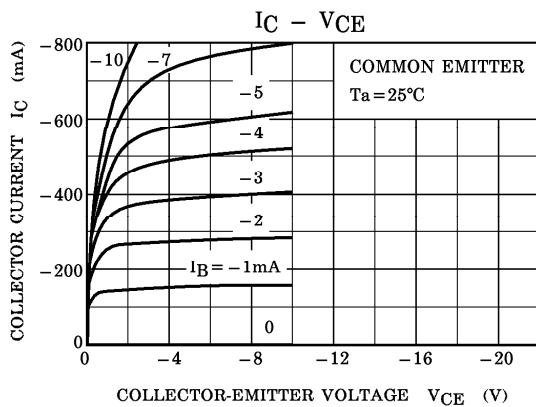
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2-5K1A

Weight : 0.05g

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